

New CCE results with microstrip detectors made on various substrates

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OUTLINE:

The charge collection efficiency of μ -strip sensors made with the RD50 mask set with various silicon substrates (n and p FZ and MCz) have been compared to different high doses of neutron and protons, well in the range of the anticipated fluences in SLHC.

Detectors: 1x1 cm⁻², Readout: SCT128, Source: ⁹⁰Sr, Temperature: ~-20/25°C.

•FZ n-in-p (10 and 30 k Ω cm⁻¹)

•FZ p-in-n

•FZ n-in-n

•MCz p-in-n

•MCz n-in-n

•Epi p-in-n

•Epi n-in-n

•Various thicknesses FZ n-in-p and n-in-n

Irradiation

Many thanks to our RD50 collaborators:

Neutron irradiations, our gracious guests: JSI of Ljubljana (V. Cindro et al.).

24GeV/c protons, CERN/PS: M. Glaser et al.

26 MeV protons Karlsruhe (W. de Boer et al).

Neutron irradiations: low doses (1x10¹⁴ n cm⁻²)



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Neutron irradiations: still low doses (2x10¹⁴ n cm⁻²)

Epi detector irradiated to 3x10¹⁴ cm⁻²).



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Neutron irradiations: low/medium doses (5x10¹⁴ n cm⁻²)



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Neutron irradiations: medium doses (1x10¹⁵ n cm⁻²)



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Neutron irradiations: medium/high doses (1.6x10¹⁵ n cm⁻²)



Bias (V)

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Neutron irradiations: high doses (3x10¹⁵ n cm⁻²)



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Neutron irradiations: very high doses (1x10¹⁶ n cm⁻²)

Epi detector irradiated to 8x10¹⁵ cm⁻²).



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Summary neutron irradiation

Thin vs thick: no sensitive difference even after 10¹⁶ cm⁻². Choice of thickness left to considerations other than radiation hardness.

- Only significant improvement: n-MCz, which adds lower degradation of N_{eff} with Φ , to the advantage obtained by going through type inversion.
- No significant advantage seen with epi n or p, although p-in-n epi shows a much bigger signal than other p-in-n sensors.

24GeV/c proton irradiations

N-side readout vs p-in-n



24GeV/c proton irradiations



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Thin vs thick, n vs p substrate, neutron and 24GeV/c proton irradiations





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24GeV/c proton irradiations vs neutron



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Low energy proton irradiations: comparison (with 24GeV/c p) of CCE for NIEL equivalent doses



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Low energy proton irradiations: comparison (with rector neutron) of CCE for NIEL equivalent doses

1x10¹⁶ cm⁻²!



Low energy proton irradiations vs neutron



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Special effects: mixed irradiations (neutrons + protons)

